Ultra Low-Dielectric Loss SSBS and CCI for Beyond 5G

Ultra Low-Dielectric Loss SSBS Characteristic

We have developed Low-dielectric compositions based on JSR's low-dielectric resin. It showed high potential in all Dk, Df, Tg and Water absorption.

With the above developments, we are now able to offer superior low-dielectric-loss materials.

SSBS Composition

[For M-SAP]



- Copper: t = 1.5 µm
- Low Dielectric Adhesive: t = 25 μm

[For Subtractive]



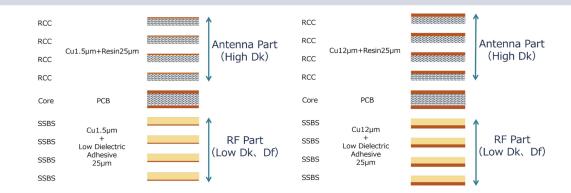
- Copper: t = 12 μm
- Low Dielectric Adhesive: t = 25 μm

Typical Values

Item	Unit	SSBS
Dk / Df	10GHz	2.55 / 0.0019
Tg (DMA)	°C	170.5
Peel strength	N/mm	0.72
Solder heat resistance (T288)	sec.	>300
Folding endurance A (D=3.0mm)	times	>100
Water absorption	%	0.2
UL 94		V-0(Equiv.)

** The values mentioned above are example of laboratory experiences and are not value of standard.

Main SSBS Layer Structure for AiP



Ultra Low-Dielectric Loss & Low CTE CCL Characteristic

CCL Composition

[Major Characteristic]

·Si-filler less



- · Copper: t = 18 µm
- Specialty Cloth: t = 27 μm

Typical Values

Item	Unit	CCL
Dk / Df	10GHz	2.45 / 0.0017
Tg (DMA)	°C	170.5
Peel strength	N/mm	0.68
CTE (X/Y)	ppm/℃	10.0
Solder heat resistance (T288)	sec.	>300
Water absorption	%	0.2
UL 94		V-0(Equiv.)

** The values mentioned above are example of laboratory experiences and are not value of standard.



